DIC L15: Delay (3)

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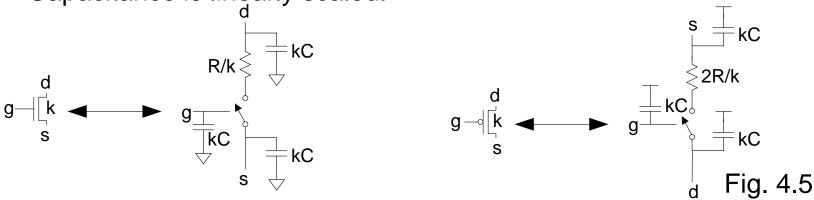
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4.3. RC delay model (1)

- Easily estimate the delay
- RC delay models approximate the nonlinear transistor IV and CV characteristics with an average resistance and capacitance over the switching range of the gate.
 - Total capacitance on output node: C
 - Effective resistance: R
 - Propagation delay ~ RC
- Characterize transistors by finding their effective R values.
 - Not accurate, however good enough to predict RC delay

4.3. RC delay model (2)

- Equivalent R, gate and diffusion capacitance
 - Unit NMOS (for example, $4\lambda/2\lambda$) is defined to have effective resistance R. An NMOS, whose width is k times unit width, has resistance R/k.
 - Let us assume that unit PMOS has effective resistance 2R.
 - Capacitance is linearly scaled.



4.3. RC delay model (3)

A fanout-of-1 inverter

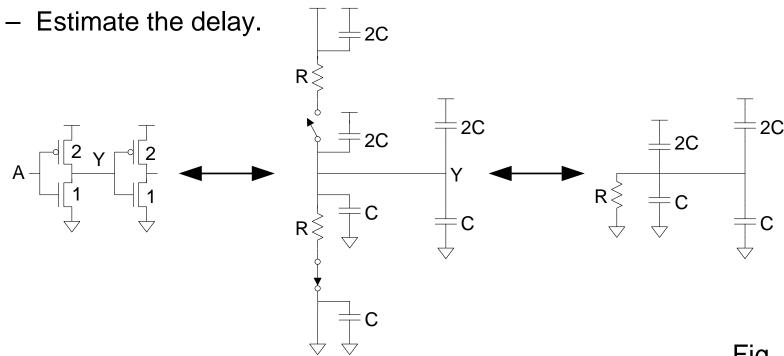
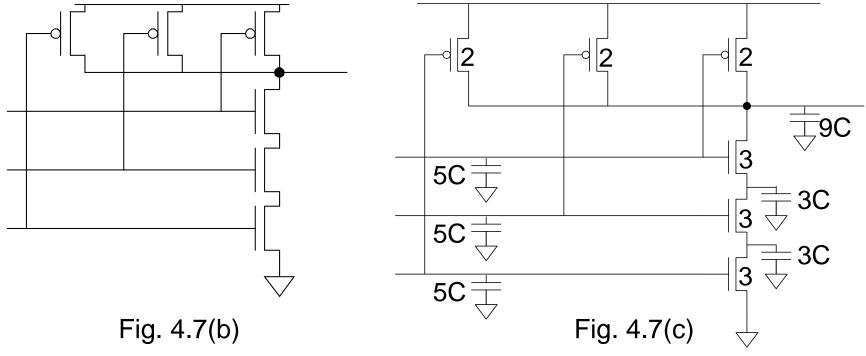


Fig. 4.6

4.3. RC delay model (4)

• Example 4.2



4.3. RC delay model (5)

- First-order RC circuit
 - Its output voltage follows

$$V_{out}(t) = V_{DD} \exp\left(-\frac{t}{RC}\right)$$
 Eq. (4.7)

Then, the propagation delay becomes

$$t_{pd} = RC \ln 2$$

Eq. (4.8)

Eq. (4.11)

Second-order RC circuit

$$V_{out}(t) = V_{DD} \frac{\tau_1 e^{-t/\tau_1} - \tau_2 e^{-t/\tau_2}}{\tau_1 - \tau_2}$$

How about general RC tree circuits?

4.3. RC delay model (6)

- Elmore delay
 - A simple single time constant approximation

4.3. RC delay model (7)

• Example 4.7

